

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

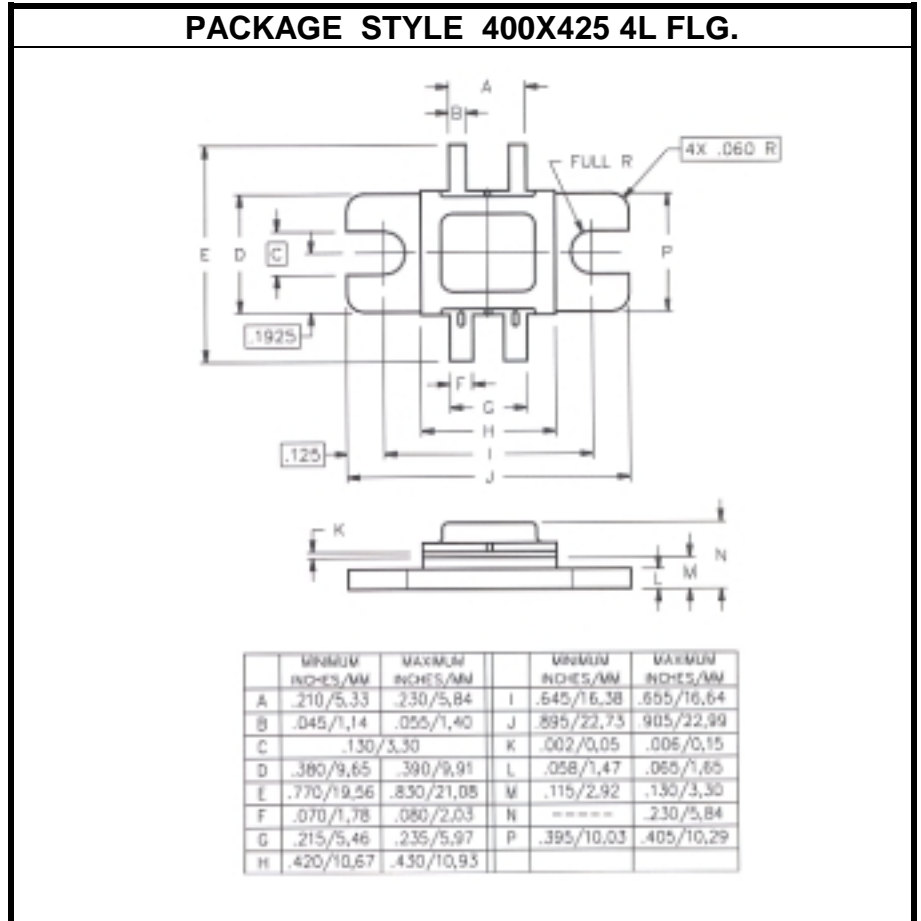
The **ASI MRA0510-50H** is Designed for Class AB Linear Amplifier Applications up to 1000 MHz.

FEATURES:

- **Omnigold™** Metalization System
- Diffused Ballast Resistors.
- Internal Matching Network

MAXIMUM RATINGS

V_{CEO}	30 V
V_{CBO}	60 V
V_{EBO}	4.0 V
P_{DISS}	125 W @ T _C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +200 °C
θ_{JC}	1.4 °C/W


CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CES}	I _C = 25 mA	60			V
BV_{CBO}	I _C = 25 mA	60			V
BV_{EBO}	I _E = 5.0 mA	4.0			V
I_{CBO}	V _{CB} = 30 V			25	mA
h_{FE}	V _{CE} = 5.0 V I _C = 1.0 A	20		80	---
C_{ob}	V _{CB} = 28 V f = 1.0 MHz			24	pF
G_{PB} VSRW	V _{CE} = 28 V P _{out} = 50 W I _{CQ} = 2 X 120 mA f = 1.0 GHz	7.0 5:1			dB ---